

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

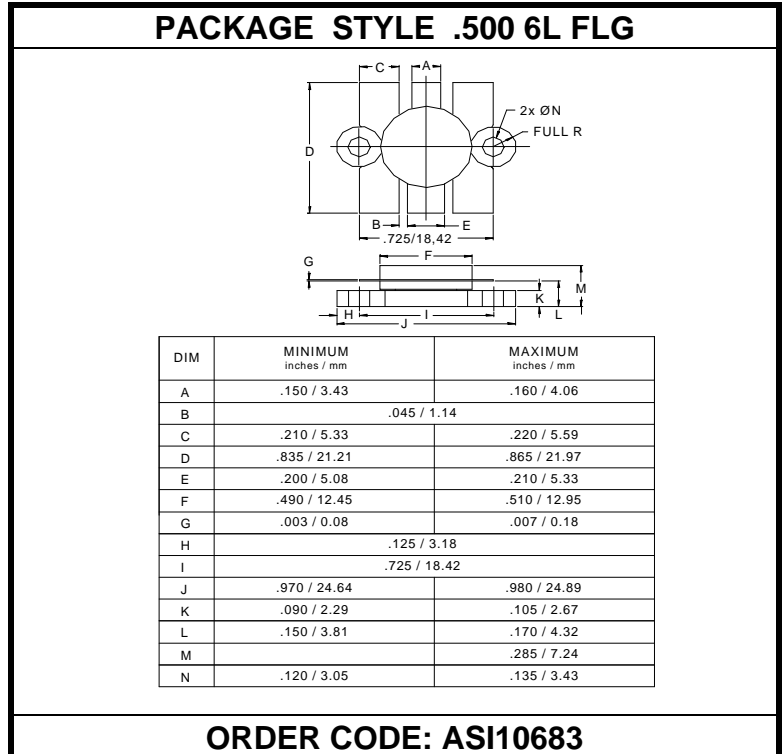
The ASI ULBM25 is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	4.8 A
<b>V<sub>CB0</sub></b>	36 V
<b>V<sub>CEO</sub></b>	16 V
<b>V<sub>CES</sub></b>	36 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	70 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	2.5 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	16			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 10 mA	36			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 5.0 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 12.5 V			5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	10		---	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 12.5 V      f = 1.0 MHz			80	<b>pF</b>
<b>P<sub>G</sub></b> <b>η<sub>C</sub></b>	V <sub>CC</sub> = 12.5 V      P <sub>OUT</sub> = 25 W      f = 470 MHz	6.5	60		<b>dB</b> <b>%</b>